AUTOMOTIVE

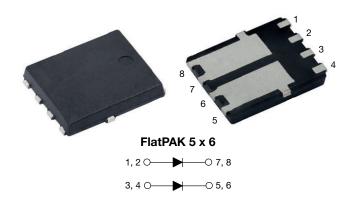
COMPLIANT HALOGEN

FREE



Vishay Semiconductors

Hyperfast Rectifier, 2 x 4 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS							
I _{F(AV)} 2 x 4 A							
V_{R}	200 V						
V _F at I _F	0.7 V						
t _{rr (typ.)}	25 ns						
T _J max.	175 °C						
Package	FlatPAK 5 x 6						
Circuit configuration	Separated cathode						

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- AEC-Q101 qualified
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V_{RRM}		200	V			
Average rectified forward current	nor dovice	I _{F(AV)}	T _{Solderpad} = 170 °C, DC	- 8	^			
	per device		T _{Solderpad} = 169 °C, D = 0.5					
Non-repetitive peak surge current —	per device	1	T 05 %C 10 mm simus sidel mules	173	Α			
	per diode	I _{FSM}	T _J = 25 °C, 10 ms sinusoidal pulse	87				
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	200	-	-			
Forward voltage, per diode	V_{F}	I _F = 4 A	-	0.87	0.96	V		
		I _F = 4 A, T _J = 150 °C	-	0.7	0.78			
Reverse leakage current, per diode	I _R	$V_R = V_R$ rated	-	-	2			
		T _J = 150 °C, V _R = V _R rated	-	7	80	- μΑ		
Junction capacitance	C_{T}	V _R = 200 V	-	19	-	pF		



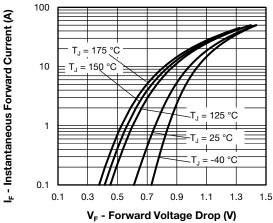
DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, dI_F/dt =$	= 50 A/ μ s, V _R = 30 V	ı	20	-			
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		i	ı	25			
	t _{rr}	T _J = 25 °C		Ī	17	-	ns		
		T _J = 125 °C		ı	29	-			
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 4 A dI _F /dt = 200 A/μs V _B = 160 V	ı	2.1	-	Α		
Peak recovery current		T _J = 125 °C		Ī	4	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	18	-	200		
		T _J = 125 °C		-	60	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	=	175	°C			
Thermal resistance, junction to ambient, per diode	R _{thJA} (1)(2)		-	89	103	°C/W			
Thermal resistance, junction to mount, per diode	R _{thJM} (3)		-	1.8	2.1	G/VV			

Notes

- $^{(1)}$ The heat generated must be less than the thermal conductivity from junction to ambient: $dP_D/dT_J < 1/R_{thJA}$
- (2) Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} junction to ambient
- (3) Mounted on infinite heatsink







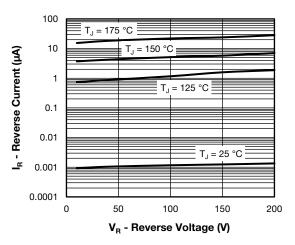


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

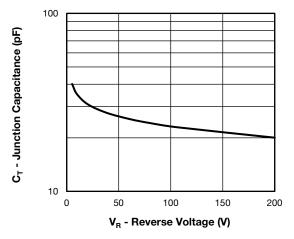


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

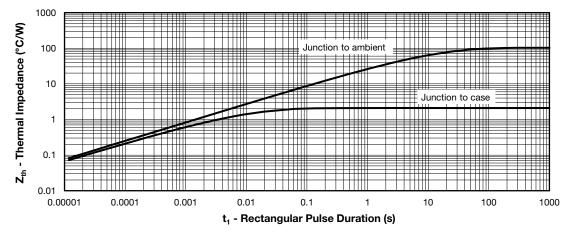


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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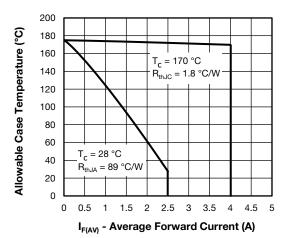
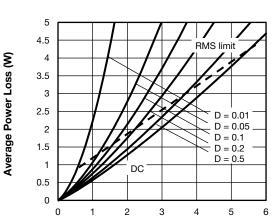


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



I_{F(AV)} - Average Forward Current (A)
Fig. 6 - Forward Power Loss Characteristics

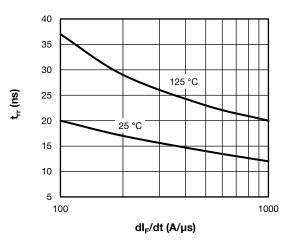


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

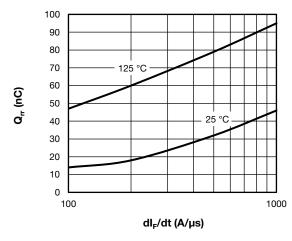
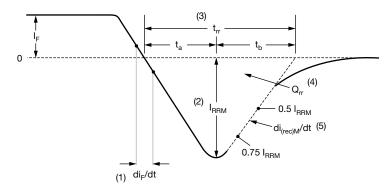


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

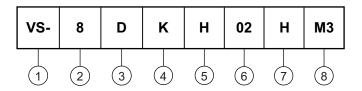
(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

3 - Circuit configuration:

D = separated cathode

K = FlatPAK package

5 - Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

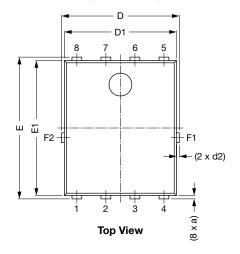
ORDERING INFORMATION (example)								
PREFERRED P/N UNIT WEIGHT (g) PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING								
VS-8DKH02HM3/H	0.10	Н	1500	7"diameter plastic tape and reel				
VS-8DKH02HM3/I	0.10	I	6000	13"diameter plastic tape and reel				

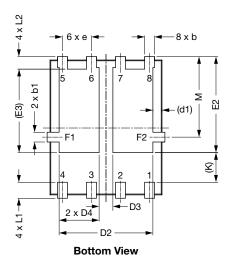
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96056</u>						
Part marking information	www.vishay.com/doc?96059					
Packaging information	www.vishay.com/doc?88869					

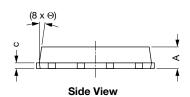


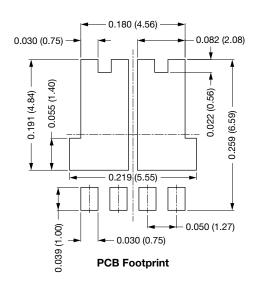
FlatPAK 5 x 6 (Dual)

DIMENSIONS in inches (millimeters)









DIM		INCHES			MILLIMETERS	3
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.035	0.039	0.043	0.89	0.99	1.09
(a)	-	0.006	=	=	0.15	=
b	0.013	0.017	0.020	0.32	0.43	0.52
b1	0.013	0.017	0.020	0.32	0.43	0.52
С	0.008	-	0.014	0.20	=	0.35
D	0.197	0.203	0.209	5.00	5.15	5.30
D1	0.189	0.193	0.197	4.80	4.90	5.00
D2	0.154	0.161	0.169	3.90	4.10	4.30
D3	0.020	0.024	0.031	0.50	0.60	0.80
D4	0.063	0.069	0.075	1.60	1.75	1.90
(d1)	-	0.016	=	=	0.40	=
(d2)	-	0.005	-	=	0.125	-
E	0.238	0.244	0.250	6.05	6.20	6.35

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Outline Dimensions

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DIM.		INCHES			MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	=	-	3.65	=		
е		0.050 BSC		1.27 BSC				
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
M	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

Notes

- Dimensioning and tolerancing per ASME Y14.5-2009
- Dimensions D1 and E1 do not include mold flash or gate burrs
- Dimension (XX) means reference only



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